

DESCRIPTION

The XPX444FD is N channel enhancement mode power effect transistor which is produced using high cell density advanced trench technology.

The high density process is especially able to minimize on-state resistance. These devices are especially suited for low voltage application power management DC-DC converters.

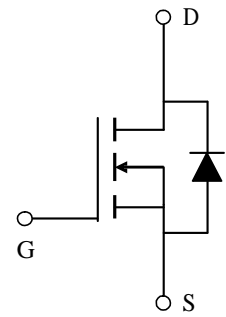
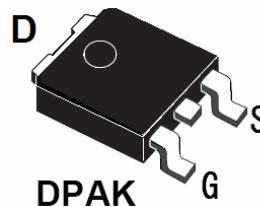
APPLICATIONS

- ◆ Power Management
- ◆ DC/DC Converter
- ◆ Load Switch

FEATURE

- ◆ 60V/28A, $R_{DS(ON)}=22m\Omega(typ.)@VGS=10V$
- ◆ 60V/18A, $R_{DS(ON)}=28m\Omega(typ.)@VGS=4.5V$
- ◆ Super high design for extremely low $R_{DS(ON)}$

PIN CONFIGURATION



ORDERING INFORMATION

Part Number	Package Code	Package	Shipping
XPX444FD AT-TRG	T	TO-252	2500EA / T&R

- ※ Year Code : 0~9
- ※ Week Code : A~Z(1-26); a~z(27~52)
- ※ G : Green Product. This product is RoHS compliant.

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless otherwise noted)

Symbol	Parameter	Max.	Units
VDS	Drain-to-Source Voltage	60	V
VGS	Gate-to-Source Voltage	± 20	
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V$	15	A
$I_D @ T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V$	12	
$I_D @ T_C(\text{Bottom}) = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V$	28	
$I_D @ T_C(\text{Bottom}) = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V$	18	
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V$ (Package Limited)	12	
I_{DM}	Pulsed Drain Current	30	
$P_D @ T_A = 25^\circ\text{C}$	Power Dissipation	2.1	W
$P_D @ T_C(\text{Bottom}) = 25^\circ\text{C}$	Power Dissipation	20	
	Linear Derating Factor	0.03	W/ $^\circ\text{C}$
T_J	Operating Junction and	-55 to + 150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range		

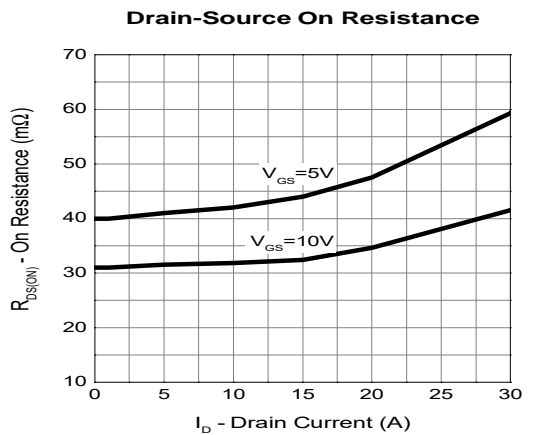
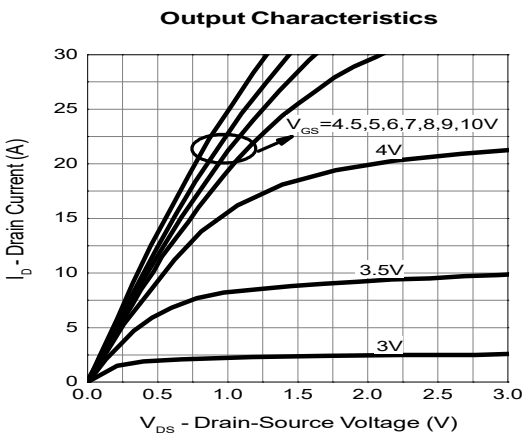
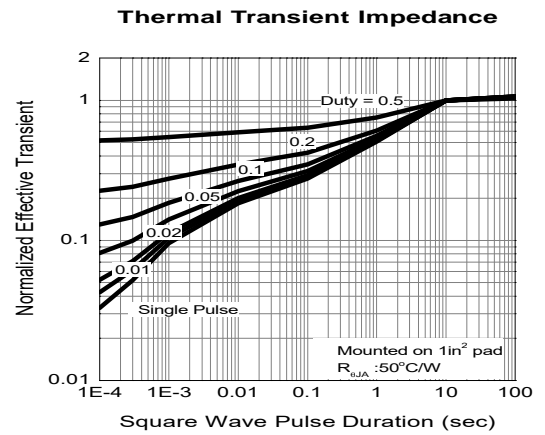
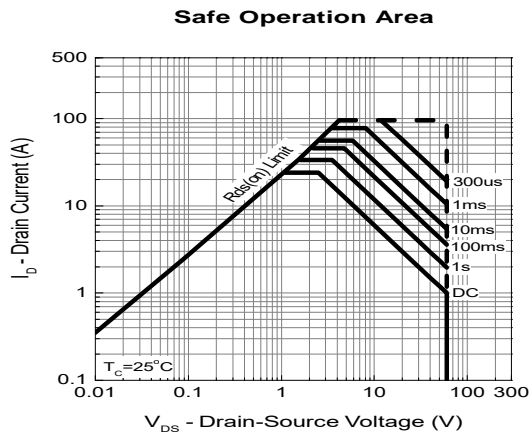
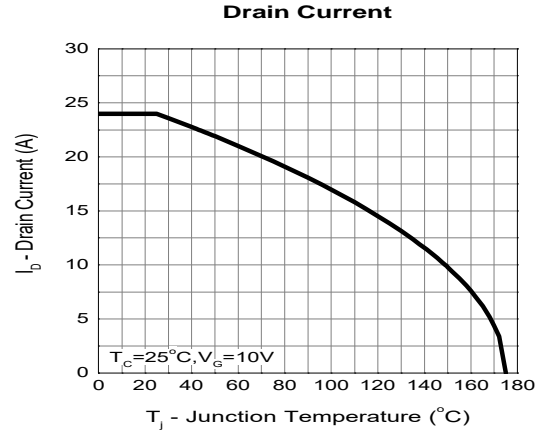
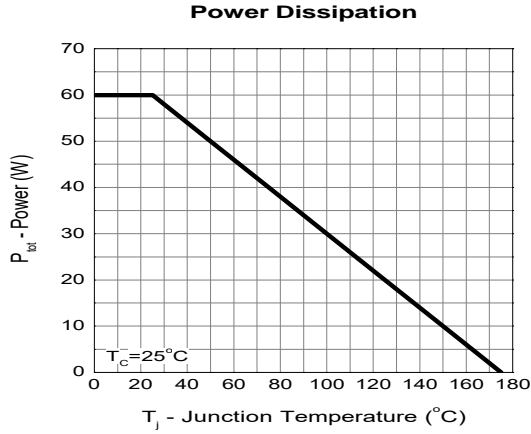
■ ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ Unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Parameters						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0		3.0	V
I_{GSS}	Gate Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=48V, V_{GS}=0$			1	uA
		$V_{DS}=48V, V_{GS}=0$ $T_J=85^{\circ}\text{C}$			5	
$R_{DS(ON)}$	Drain-Source On-Resistance	$V_{GS}=10V, I_D=28A$		22	28	m Ω
		$V_{GS}=4.5V, I_D=18A$		28	35	
Source-Drain Diode						
V_{SD}	Diode Forward Voltage	$I_S=1A, V_{GS}=0V$		0.7	1.3	V
Dynamic Parameters						
Q_g	Total Gate Charge	$V_{DS}=30V$ $V_{GS}=10V$ $I_D=12A$		9		nC
Q_{gs}	Gate-Source Charge			1.6		
Q_{gd}	Gate-Drain Charge			1.8		
C_{iss}	Input Capacitance	$V_{DS}=30V$ $V_{GS}=0V$ $f=1\text{MHz}$		540		pF
C_{oss}	Output Capacitance			74		
C_{riss}	Reverse Transfer Capacitance			34		
$T_{d(on)}$	Turn-On Time	$V_{DS}=30V$ $I_D=5A$ $V_{GEN}=10V$ $R_G=3.0\Omega$		6		nS
T_r				4.6		
$T_{d(off)}$	Turn-Off Time				22	
T_f				4		

Note: 1. Pulse test: pulse width \leq 300uS, duty cycle \leq 2%

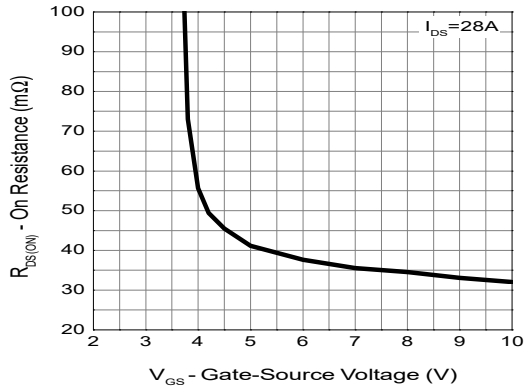
2. Static parameters are based on package level with recommended wire bonding

■ **TYPICAL CHARACTERISTICS** (25°C Unless Note)

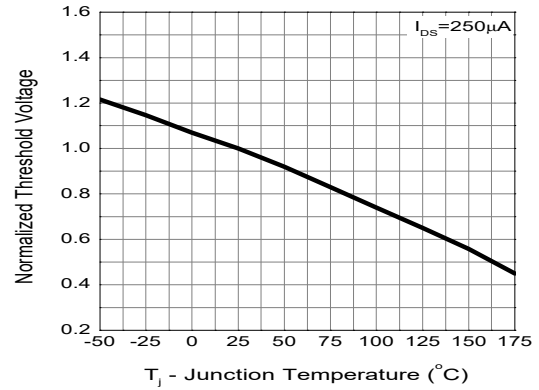


■ **TYPICAL CHARACTERISTICS** (continuous)

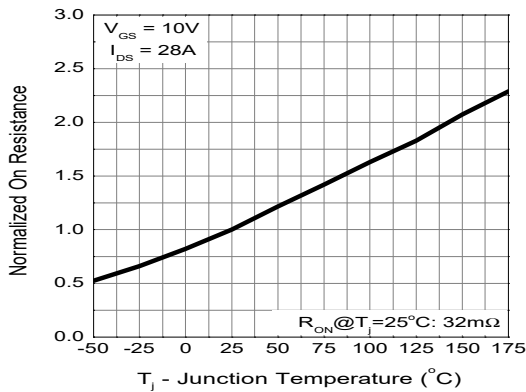
Gate-Source On Resistance



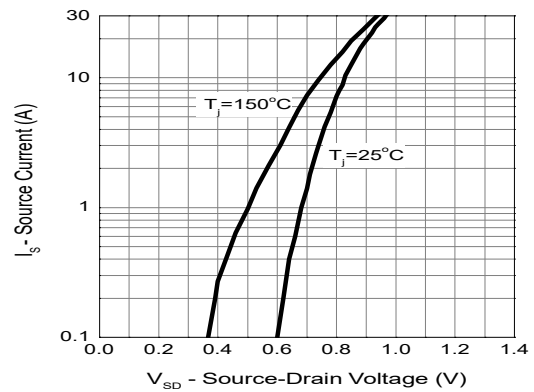
Gate Threshold Voltage



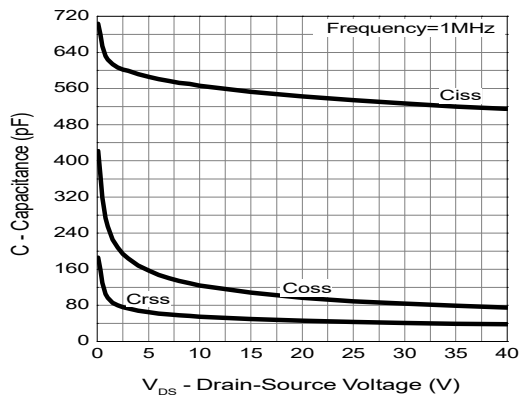
Drain-Source On Resistance



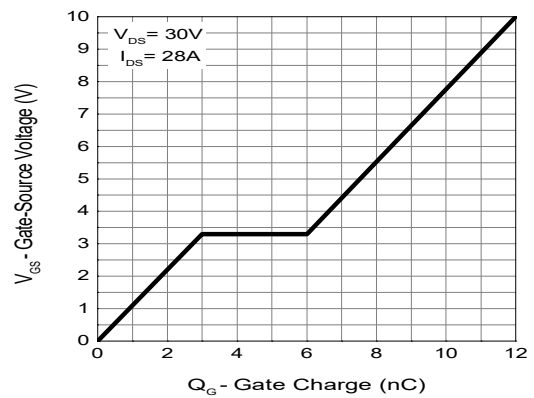
Source-Drain Diode Forward



Capacitance

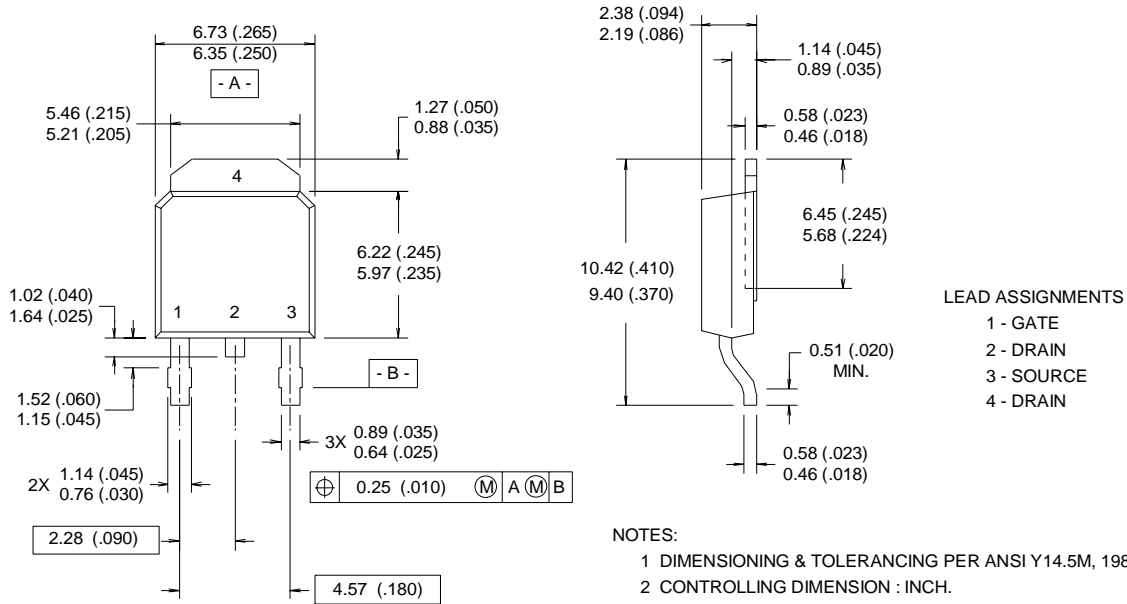


Gate Charge



TO-252 Outline Package Dimension

Dimensions are shown in millimeters (inches)

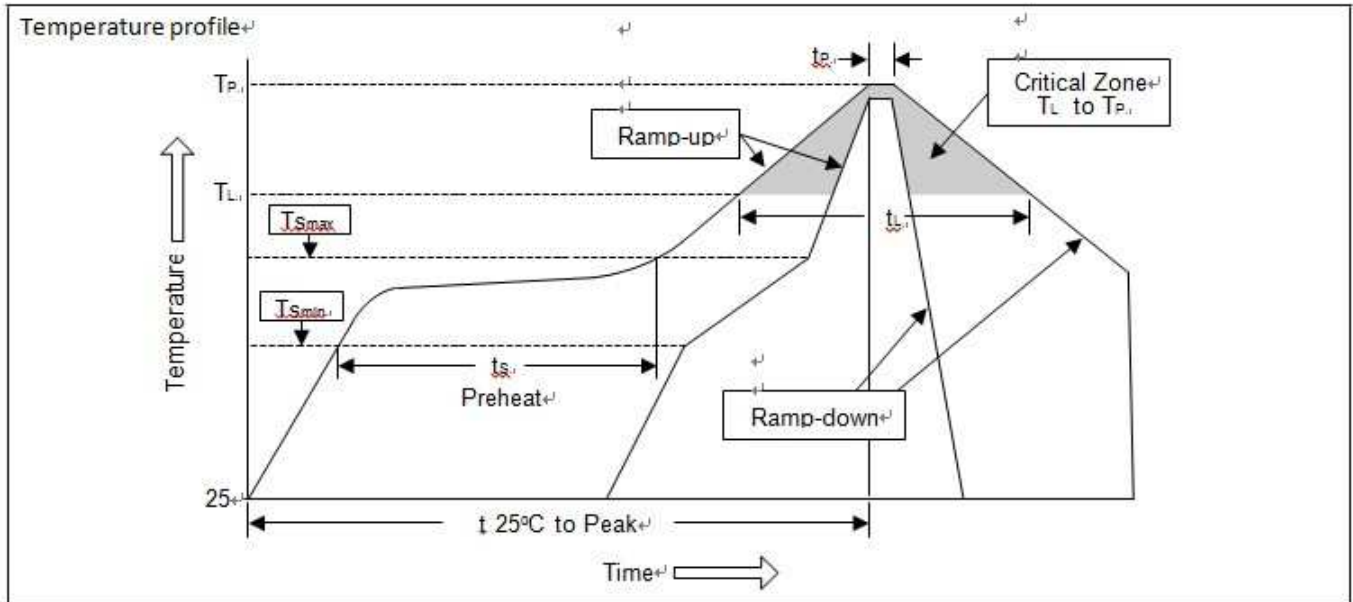


- NOTES:
- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
 - 2 CONTROLLING DIMENSION : INCH.
 - 3 CONFORMS TO JEDEC OUTLINE TO-252AA.
 - 4 DIMENSIONS SHOWN ARE BEFORE SOLDER DIP, SOLDER DIP MAX. +0.16 (.006).

■ SOLDERING METHODS FOR UNIVERCHIP

Storage environment Temperature=10°C~35°C Humidity=65%±15%

Reflow soldering of surface mount device



Profile Feature	Sn-Pb Eutectic Assembly	Pb free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat		
-Temperature Min (T_{Smin})	100°C	150°C
-Temperature Max (T_{Smax})	150°C	200°C
-Time (min to max) (t_s)	60~120 sec	60~180 sec
T_{Smax} to T_L		
-Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above		
-Temperature (T_L)	183°C	217°C
-Time (t_L)	60~150 sec	60~150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_p)	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<6 minutes

60V N-Channel Enhancement Mode MOSFET

Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time
Pb device	245°C ±5°C	5sec ±1 sec
Pb-Free device	260°C +0/-5°C	5sec ±1 sec



This integrated circuit can be damaged by ESD. UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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